

Description

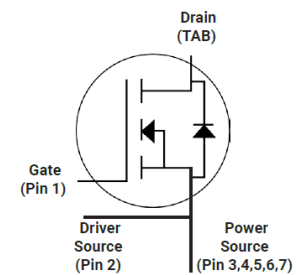
Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Optimized package with separate driver source pin
- Easy to parallel and simple to drive
- ROHS Compliant, Halogen free

**Application**

- EV Charging
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Power Factor Correction Modules

**Ordering Information**

Part Number	Marking	Package	Packaging
ASC30N1200MT7	ASC30N1200MT7	TO-263-7	Reel

ASC30N1200MT7**1200V N-Channel MOSFET****Absolute Maximum Ratings($T_c=25^{\circ}\text{C}$)**

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	1200	V
I_D	Drain Current(continuous)at $T_c=25^{\circ}\text{C}$	30	A
I_D	Drain Current(continuous)at $T_c=100^{\circ}\text{C}$	22	A
I_{DM}	Drain Current (pulsed)	80	A
V_{GS}	Gate-Source Voltage	-10/+22	V
P_D	Power Dissipation $T_c = 25^{\circ}\text{C}$	166	W
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$

Electrical Characteristics($T_J = 25^{\circ}\text{C}$ unless otherwise specified)**Typical Performance-Static**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	1200			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200\text{V},$ $V_{GS} = 0\text{V}, T_J=25^{\circ}\text{C}$			100	μA
I_{GSS}	Gate-body Leakage Current	$V_{DS} = 0\text{V} ; V_{GS} = -10 \text{ to } 20\text{V}$			250	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D=5\text{mA}$	2	3	4	V
$V_{GS(on)}$	Recommended turn-on Voltage	Static		18		V
$V_{GS(off)}$	Recommended turn-off Voltage			-5		V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS}=18\text{V}, I_D=20\text{A}$		80	100	$\text{m}\Omega$
		$V_{GS}=18\text{V}, I_D=20\text{A}$ $T_J=175^{\circ}\text{C}$		144		$\text{m}\Omega$

Typical Performance-Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS}=1000V, f=1MHz,$ $V_{AC}=25mV$		1455		pF
C_{oss}	Output Capacitance			78		pF
C_{rss}	Reverse Transfer Capacitance			3.5		pF
g_{fs}	Transconductance	$V_{DS}=20V, I_D=20A$		2.8		S
E_{OSS}	C_{OSS} Stored Energy	$V_{DS}=1000V, f=1MHz$		35.7		μJ
E_{ON}	Turn-On Energy (Body Diode)	$V_{DS}=800V, V_{GS}=-5/20V,$ $I_D=20A, L=150\mu H$ $T_J=175^\circ C$		460		μJ
E_{OFF}	Turn-Off Energy (Body Diode)			120		μJ
Q_g	Total Gate Charge	$V_{DS}=800V, V_{GS}=-5V/20V,$ $I_D = 15 A$		72		nC
Q_{gs}	Gate-source Charge			21		nC
Q_{gd}	Gate-Drain Charge			22		nC
$R_{G(int)}$	Internal Gate Resistance	$f=1MHz, V_{AC}=25mV$		5.6		Ω
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=800V, V_{GS}=-5V/20V,$ $I_D = 20A, L=150 \mu H$ $R_{ext}=2.5\Omega$		38		ns
t_r	Rise Time			13		ns
$t_{d(off)}$	Turn-off Delay Time			30		ns
t_f	Fall Time			10		ns

Typical Performance-Reverse Diode($T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FSD}	Forward Voltage	$V_{GS}=0V, I_F=10A, T_J=25^\circ C$		3.9	6	V
		$V_{GS}=0V, I_F=10A, T_J=175^\circ C$		3.5	6	V
I_S	Continuous Diode Forward Current	$V_{GS}=0V, T_C=25^\circ C$		27		A
t_{rr}	Reverse Recovery Time	$V_{GS}=-5 V, I_F=20A,$ $V_R=800 V, di/dt=900$ $A/\mu s, T_J=175^\circ C$		36		nS
Q_{rr}	Reverse Recovery Charge			297		nC
I_{rrm}	Peak Reverse Recovery Current			15.5		A

Thermal Characteristics

Symbol	Parameter	Value.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.9	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	40	$^\circ C/W$

The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of $T_J(max)=175^\circ C$

Electrical Characteristics

Fig1. Output characteristics ($T_J = 25^\circ\text{C}$)

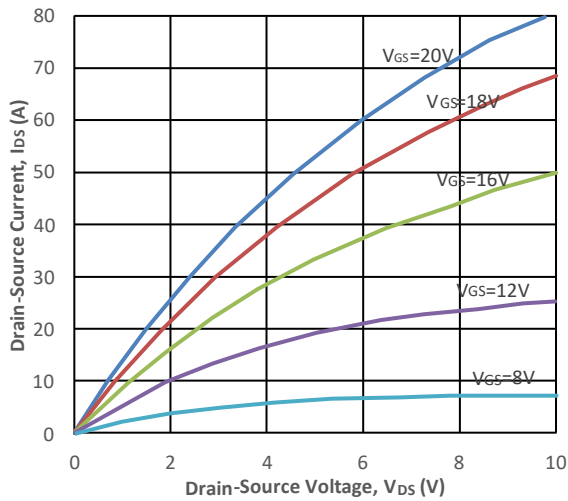


Fig2. Output characteristics ($T_J = 175^\circ\text{C}$)

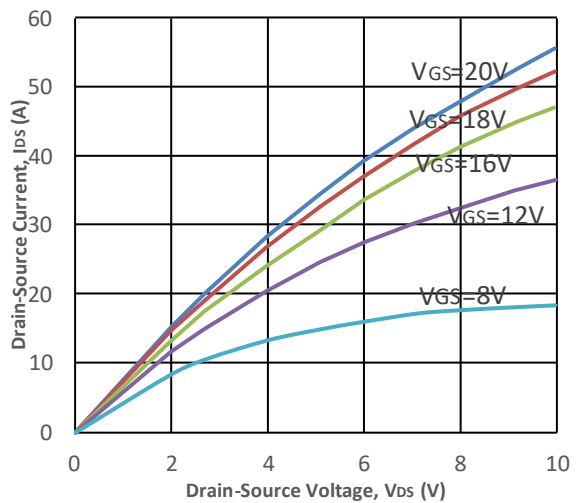


Fig3. Normalized On-Resistance vs. Temperature

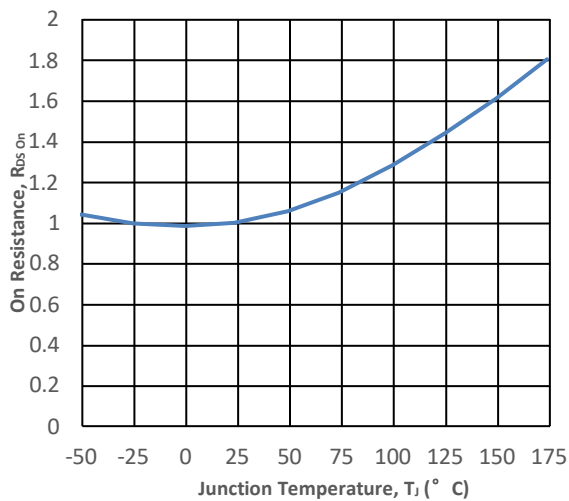


Fig4. On-Resistance vs. Temperature

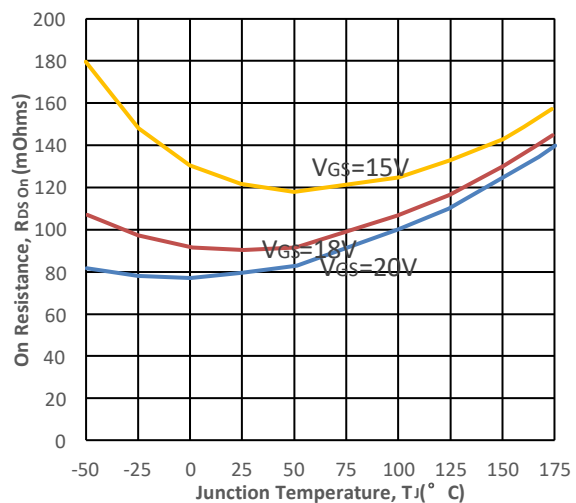


Fig5. Transfer Characteristic

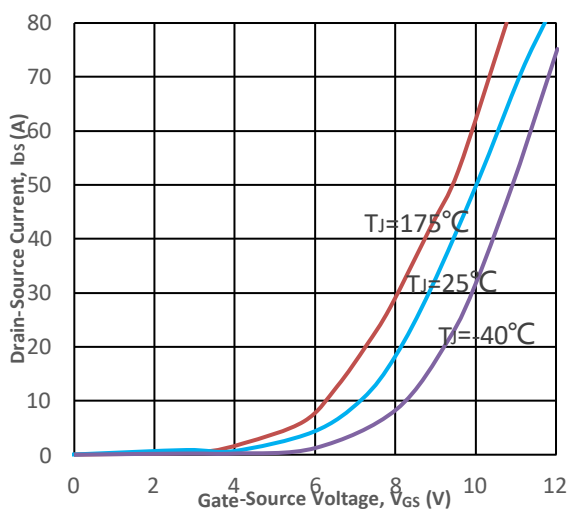


Fig6. Body Diode Characteristic at 25°C

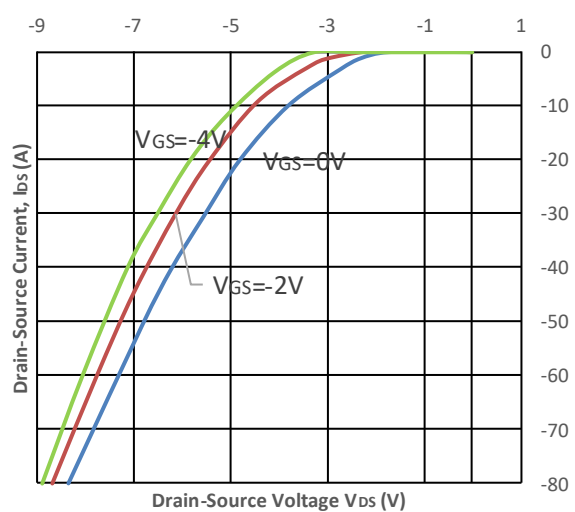


Fig7. Threshold Voltage vs. Temperature

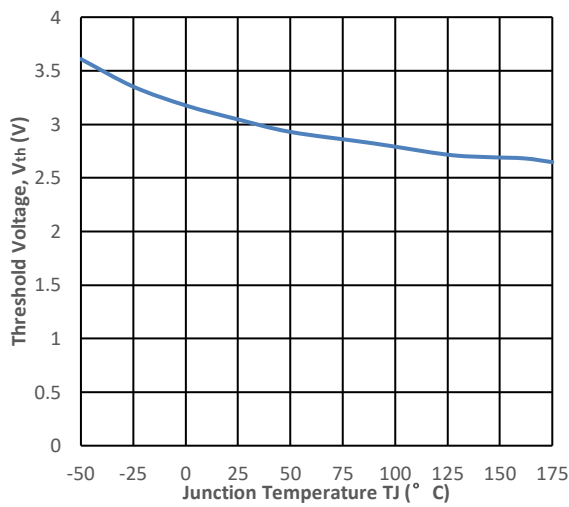


Fig8. Gate Charge Characteristics

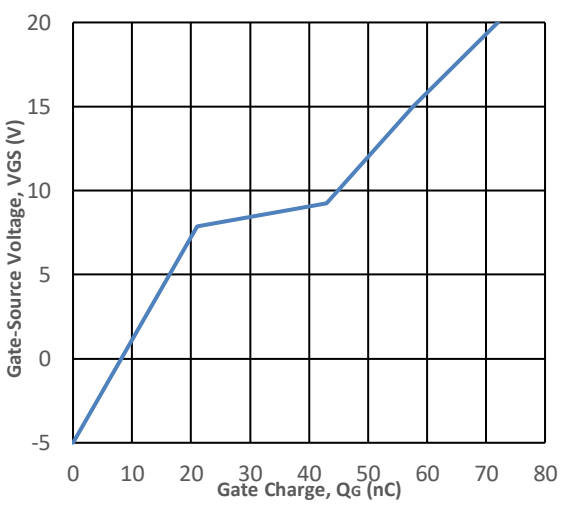


Fig9. 3rd Quadrant Characteristic at 25 $^{\circ}C$

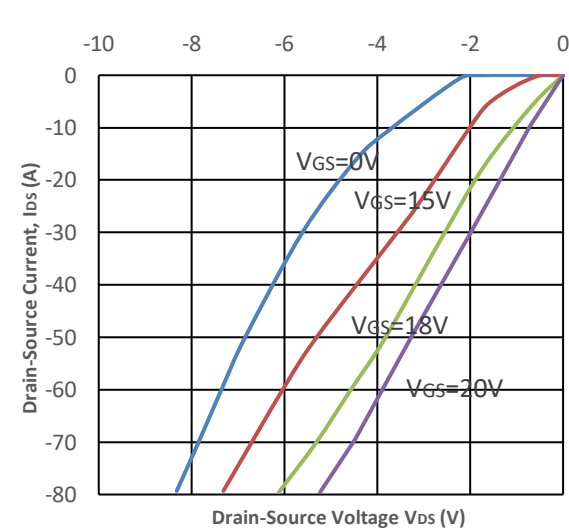


Fig10. Output Capacitor Stored Energy

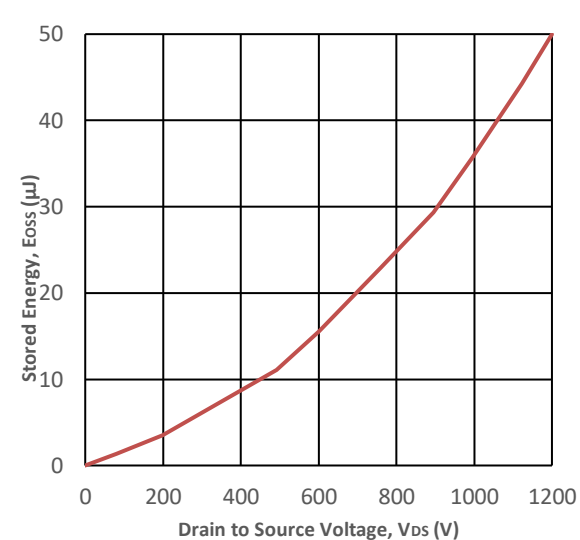


Fig11. Capacitances vs. Drain-Source

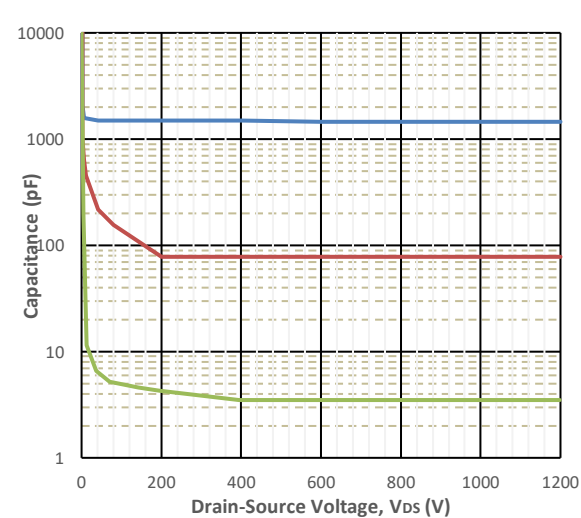


Fig12. Max Power Dissipation Derating Vs T_c

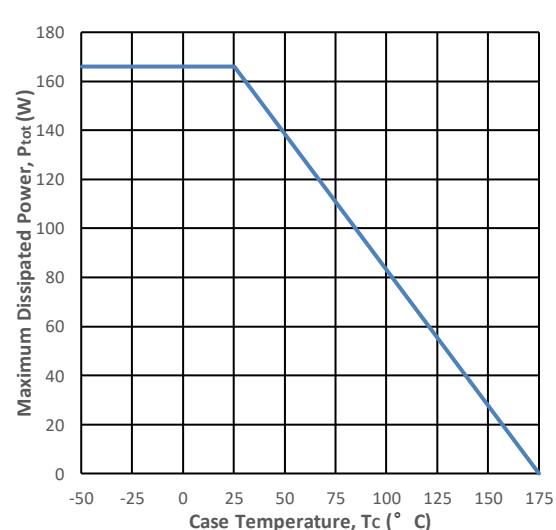


Fig13. Switching Energy vs. Drain Current

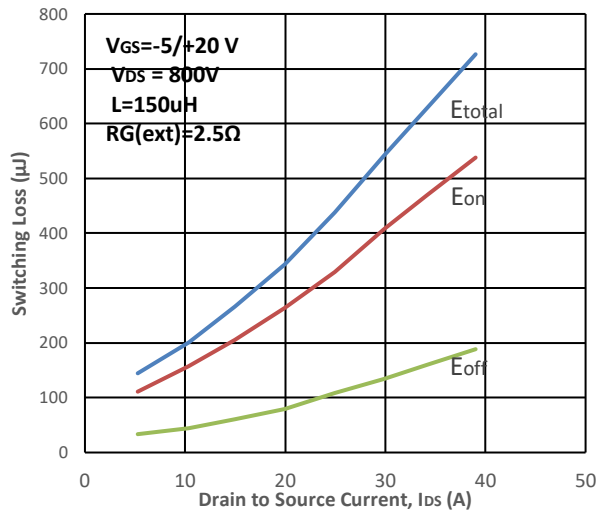


Fig14. Switching Energy vs. $R_{G(\text{ext})}$

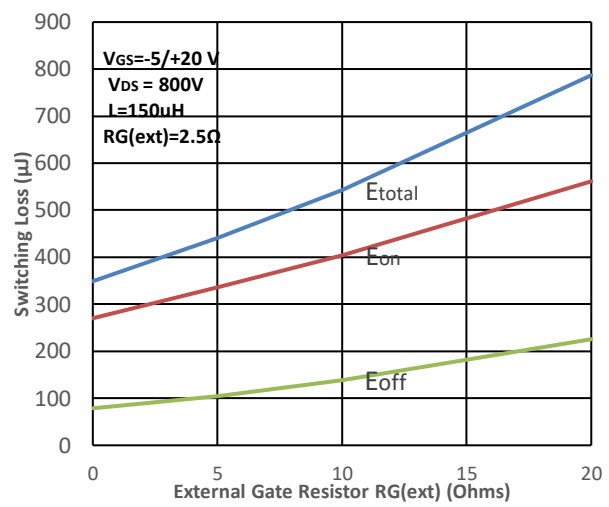


Fig15. Switching Energy vs. Temperature

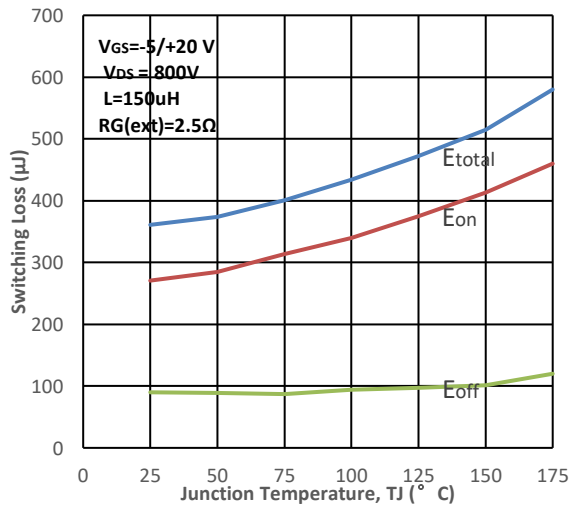


Fig16. Switching Times vs. $R_{G(\text{ext})}$

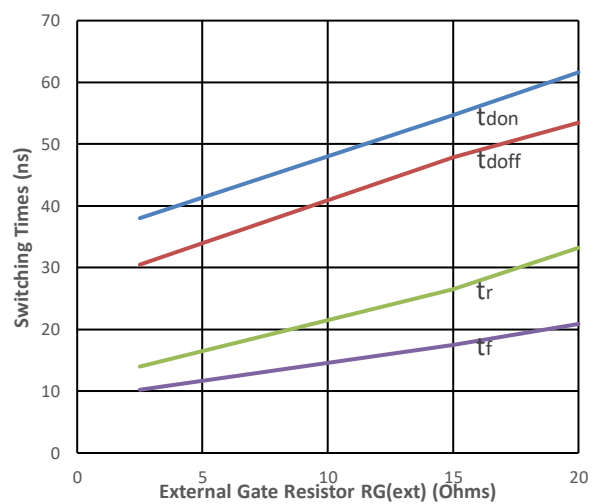


Fig17. Transient Thermal Impedance

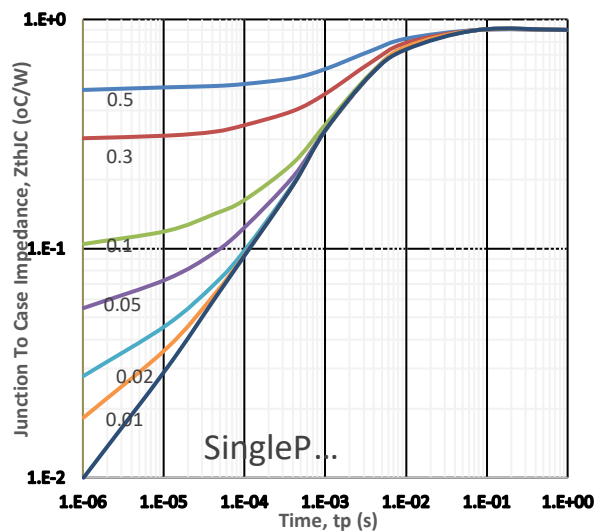
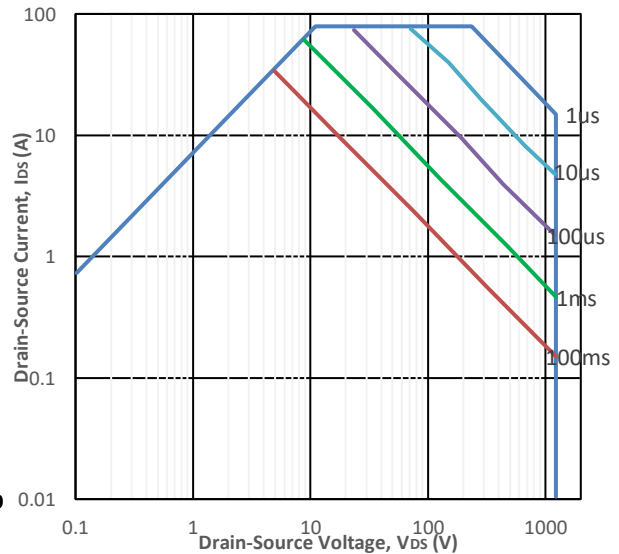
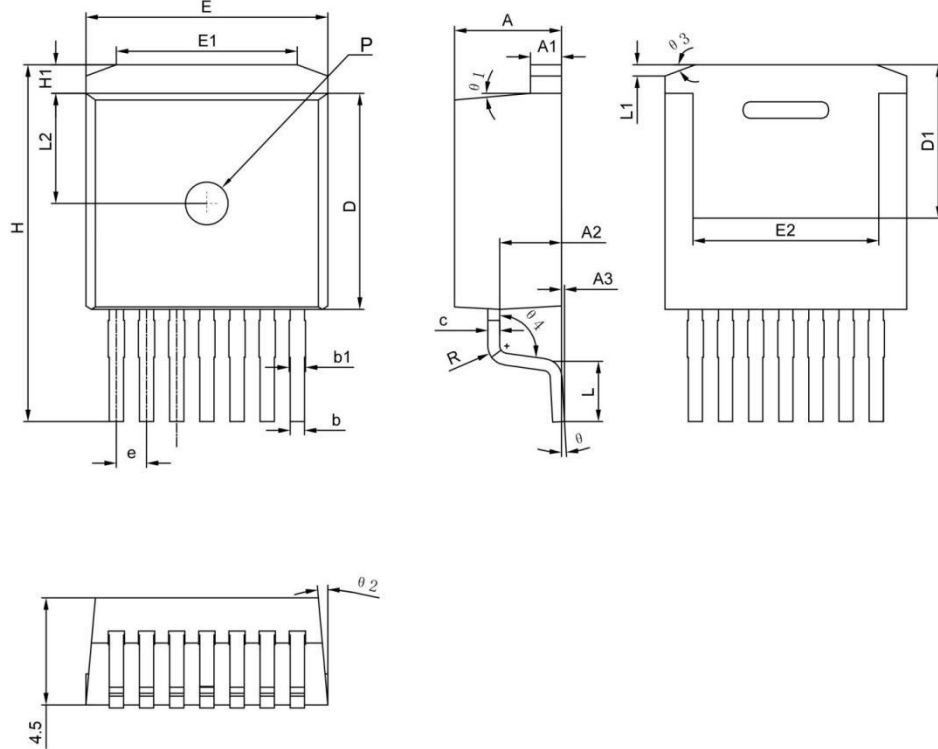


Fig18. Safe Operating Area



Package Drawing:**Dimensions: (UNIT: mm)**

SYMBOL	MIN	TYPE	MAX
A	4.40	4.50	4.60
A1	1.25	1.30	1.40
A2	2.45	2.60	2.70
A3	0.05	0.13	0.20
b	0.50	0.60	0.70
b1	0.60	0.70	0.85
c	0.45	0.50	0.60
D	8.88	9.08	9.28
D1	6.25	6.45	6.65
E	9.88	10.18	10.28
E1	6.67	7.07	7.47
E2	7.67	7.82	7.97
e	1.17	1.27	1.37
H	14.75	15.00	15.25
H1	1.10	1.20	1.30
L	2.35	2.55	2.75
L1	0.37	0.57	0.77
L2	4.48	4.63	4.78
θ	0°	3°	5°
θ1	3°	5°	7°
θ2	3°	5°	7°
θ3	15°	20°	25°
R	0.75	0.80	0.85
P	1.70	1.80	1.90

Notes:

- The information in this document is subject to change without notice.
- For more product and company information, please contact us or visit the website.

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专注

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